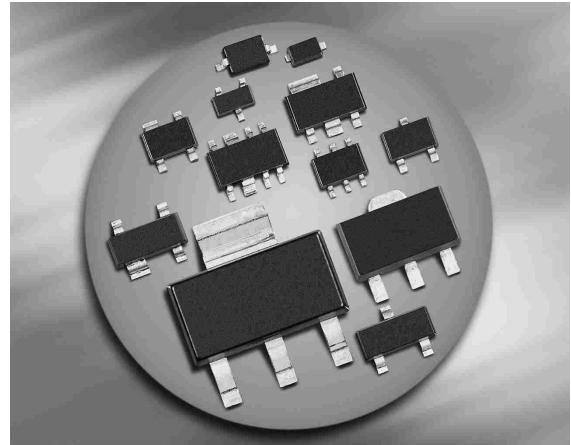
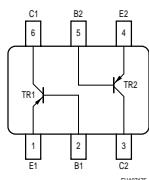


### PNP Silicon AF Transistor Arrays

- For AF input stages and driver applications
- High current gain
- Low collector-emitter saturation voltage
- Two (galvanic) internal isolated transistor with good matching in one package
- BC856S / U, BC857S: For orientation in reel see package information below
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



### BC856S/U BC857S



Type	Marking	Pin Configuration						Package
BC856S	3Ds	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363
BC856U	3Ds	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SC74
BC857S	3Cs	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage BC856S/U BC857S	$V_{CEO}$	65 45	-
Collector-base voltage BC856S, BC856U BC857S	$V_{CBO}$	80 50	V
Emitter-base voltage	$V_{EBO}$	5	
Collector current	$I_C$	100	mA
Peak collector current, $t_p \leq 10$ ms	$I_{CM}$	200	
Total power dissipation- $T_S \leq 115$ °C, BC856S $T_S \leq 118$ °C, BC856U, BC857U	$P_{tot}$	250 250	-
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-65 ... 150	

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup> BC856S, BC857S	$R_{thJS}$		K/W
BC856U		$\leq 140$ $\leq 130$	

<sup>1</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b>					
Collector-emitter breakdown voltage $I_C = 10 \text{ mA}, I_B = 0$ , BC856S/U $I_C = 10 \text{ mA}, I_B = 0$ , BC857S	$V_{(\text{BR})\text{CEO}}$	65 45	- -	- -	-
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$ , BC856S/U $I_C = 10 \mu\text{A}, I_E = 0$ , BC857S	$V_{(\text{BR})\text{CBO}}$	80 50	- -	- -	
Emitter-base breakdown voltage $I_E = 10 \mu\text{A}, I_C = 0$	$V_{(\text{BR})\text{EBO}}$	5	-	-	V
Collector-base cutoff current $V_{CB} = 45 \text{ V}, I_E = 0$ $V_{CB} = 45 \text{ V}, I_E = 0, T_A = 150^\circ\text{C}$	$I_{\text{CBO}}$	- -	- -	0.015 5	$\mu\text{A}$
DC current gain <sup>1)</sup> $I_C = 10 \mu\text{A}, V_{CE} = 5 \text{ V}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}$	$h_{\text{FE}}$	- 200	250 290	- 630	-
Collector-emitter saturation voltage <sup>1)</sup> $I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$ $I_C = 100 \text{ mA}, I_B = 5 \text{ mA}$	$V_{\text{CEsat}}$	- -	75 250	300 650	mV
Base emitter saturation voltage <sup>1)</sup> $I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$ $I_C = 100 \text{ mA}, I_B = 5 \text{ mA}$	$V_{\text{BEsat}}$	- -	700 850	- -	-
Base-emitter voltage <sup>1)</sup> $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}$	$V_{\text{BE}(\text{ON})}$	600 -	650 -	750 820	mV

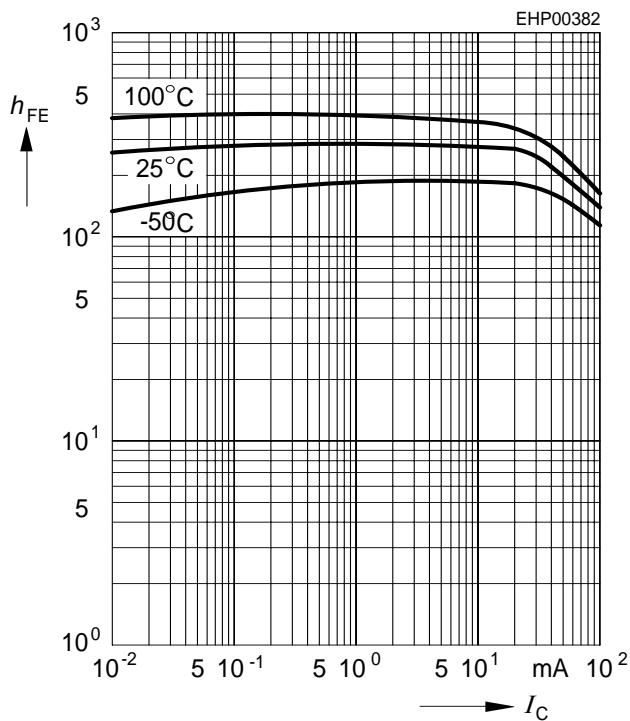
<sup>1</sup>Pulse test:  $t < 300\mu\text{s}$ ;  $D < 2\%$

**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>AC Characteristics</b>					
Transition frequency $I_C = 20 \text{ mA}, V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$	$f_T$	-	250	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	$C_{cb}$	-	1.5	-	pF
Emitter-base capacitance $V_{EB} = 0.5 \text{ V}, f = 1 \text{ MHz}$	$C_{eb}$	-	8	-	
Short-circuit input impedance $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}$	$h_{11e}$	-	4.5	-	k $\Omega$
Open-circuit reverse voltage transf. ratio $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}$	$h_{12e}$	-	2	-	$10^{-4}$
Short-circuit forward current transf. ratio $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}$	$h_{21e}$	-	330	-	-
Open-circuit output admittance $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}$	$h_{22e}$	-	30	-	$\mu\text{S}$
Noise figure $I_C = 200 \mu\text{A}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz},$ $\Delta f = 200 \text{ Hz}, R_S = 2 \text{ k}\Omega$	$F$	-	-	10	dB

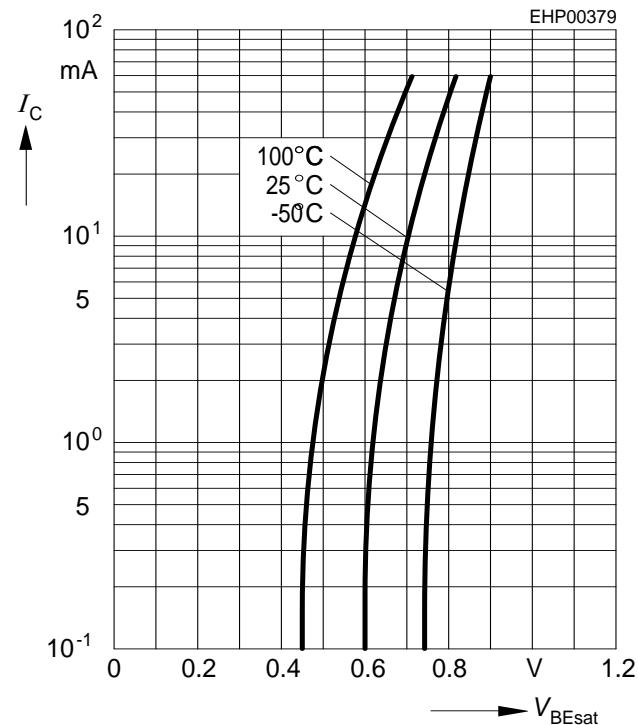
**DC current gain  $h_{FE} = f(I_C)$**

$V_{CE} = 5 \text{ V}$



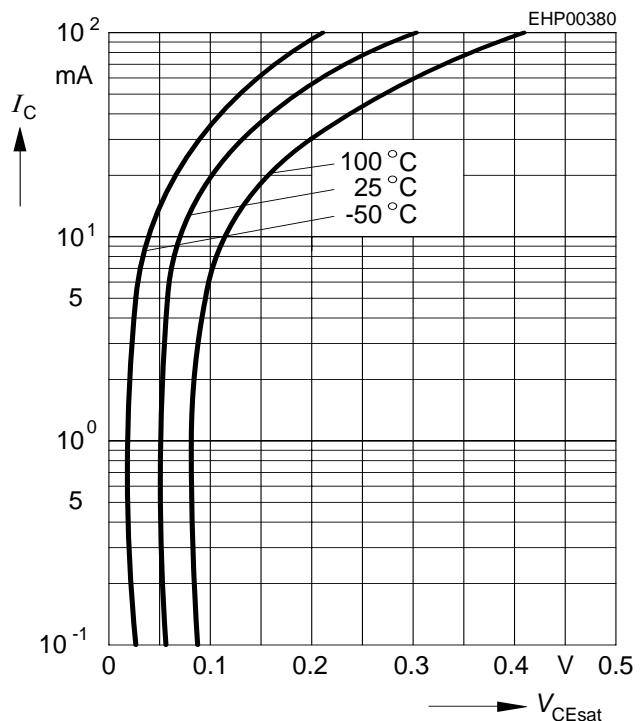
**Base-emitter saturation voltage**

$I_C = f(V_{BEsat})$ ,  $h_{FE} = 20$



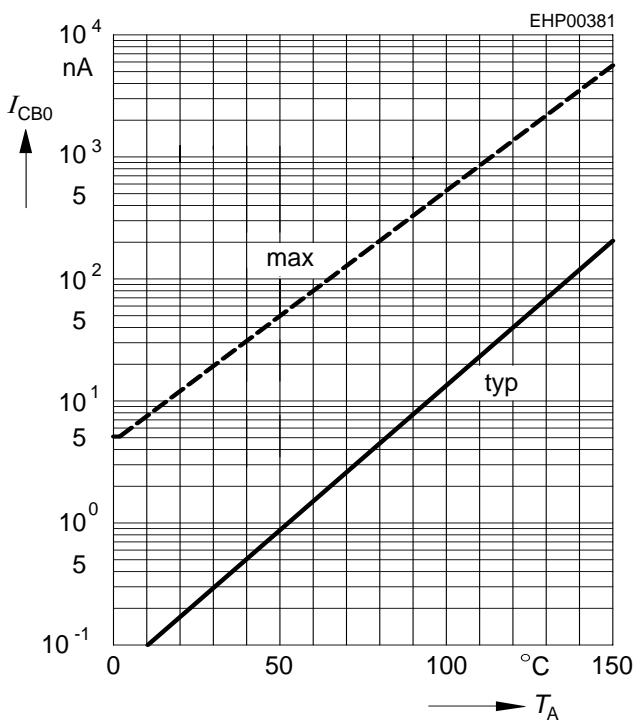
**Collector-emitter saturation voltage**

$I_C = f(V_{CEsat})$ ,  $h_{FE} = 20$

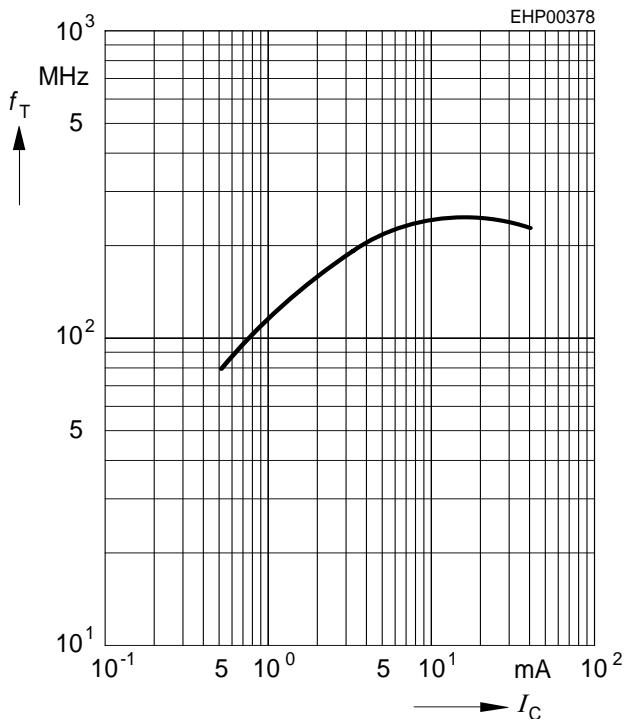


**Collector cutoff current  $I_{CBO} = f(T_A)$**

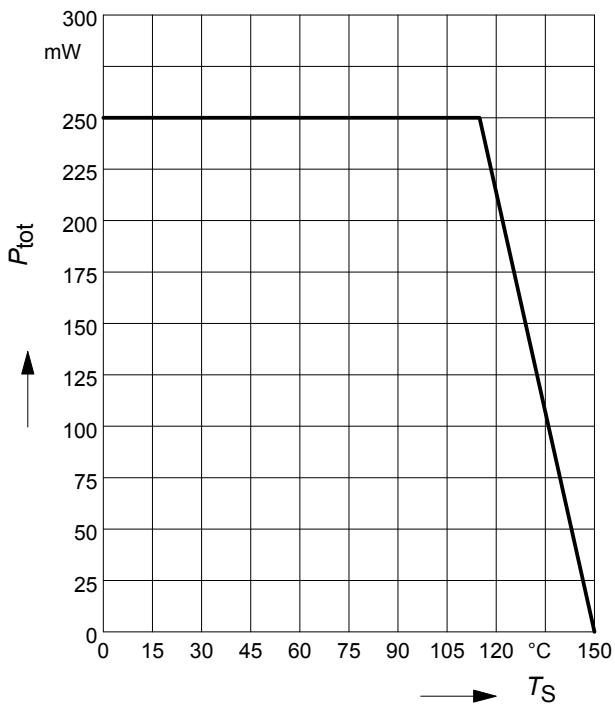
$V_{CBO} = 30 \text{ V}$



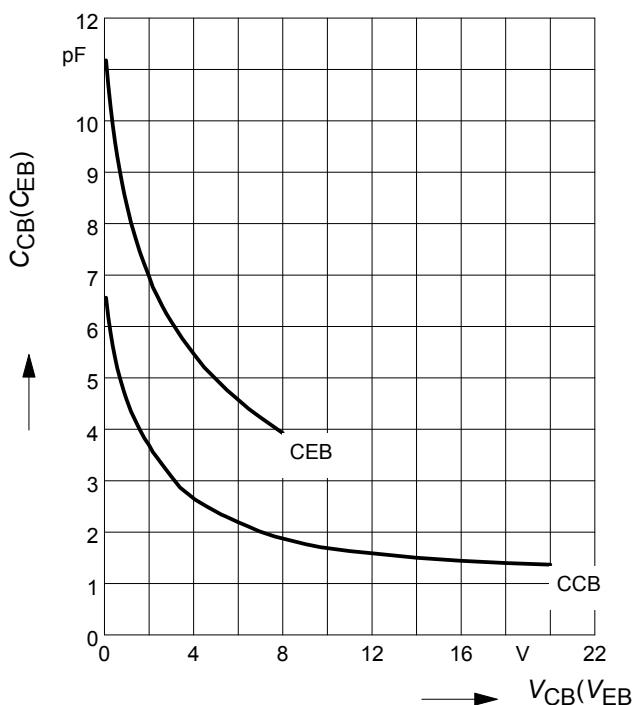
**Transition frequency**  $f_T = f(I_C)$   
 $V_{CE} = 5 \text{ V}$



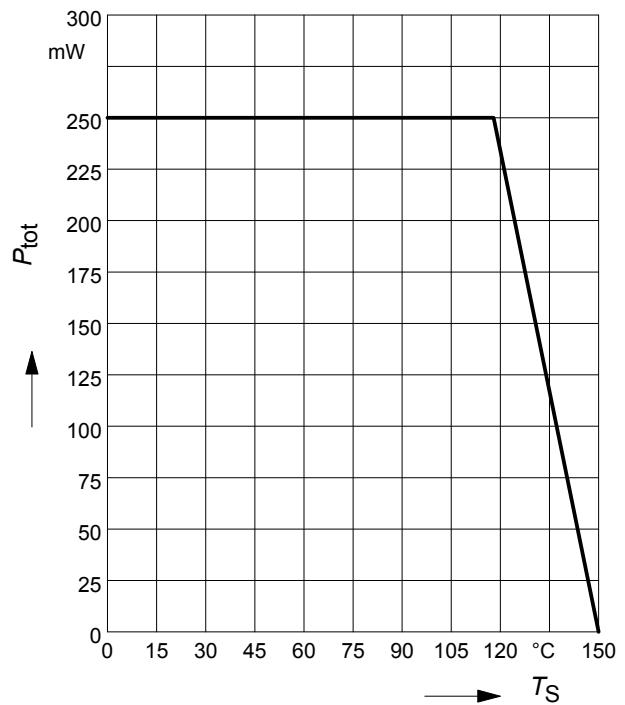
**Total power dissipation**  $P_{\text{tot}} = f(T_S)$   
BC856S, BC857S



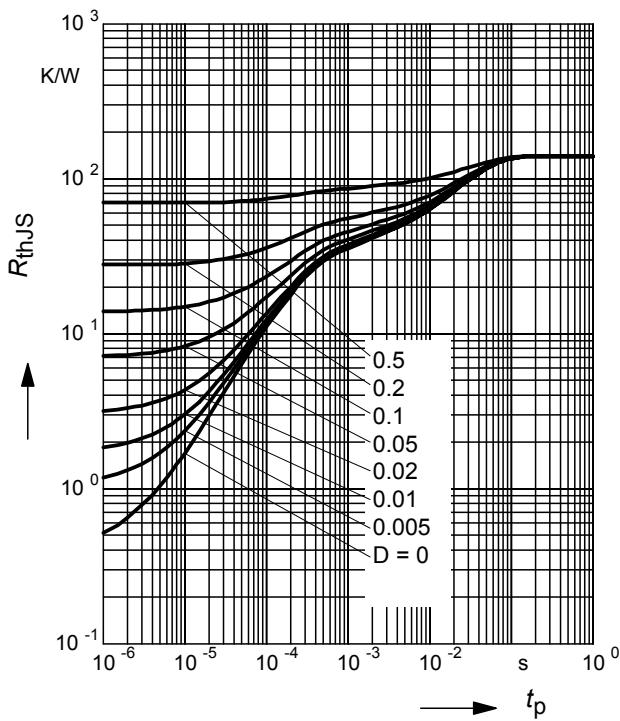
**Collector-base capacitance**  $C_{cb} = f(V_{CB})$   
**Emitter-base capacitance**  $C_{eb} = f(V_{EB})$



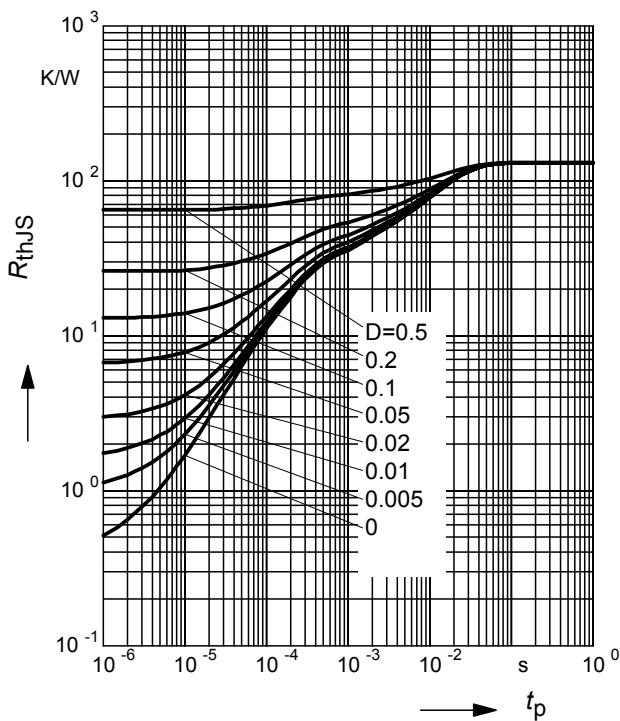
**Total power dissipation**  $P_{\text{tot}} = f(T_S)$   
BC856U



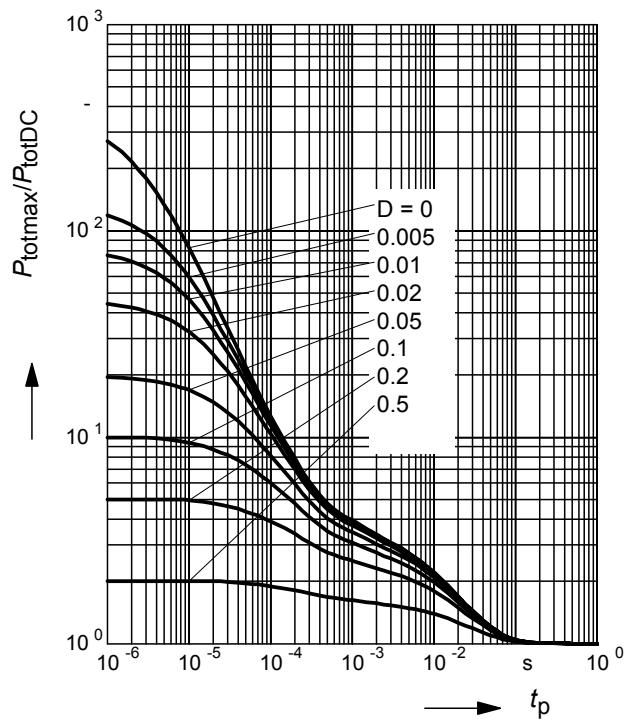
**Permissible Pulse Load**  $R_{\text{thJS}} = f(t_p)$   
BC856S; BC857S



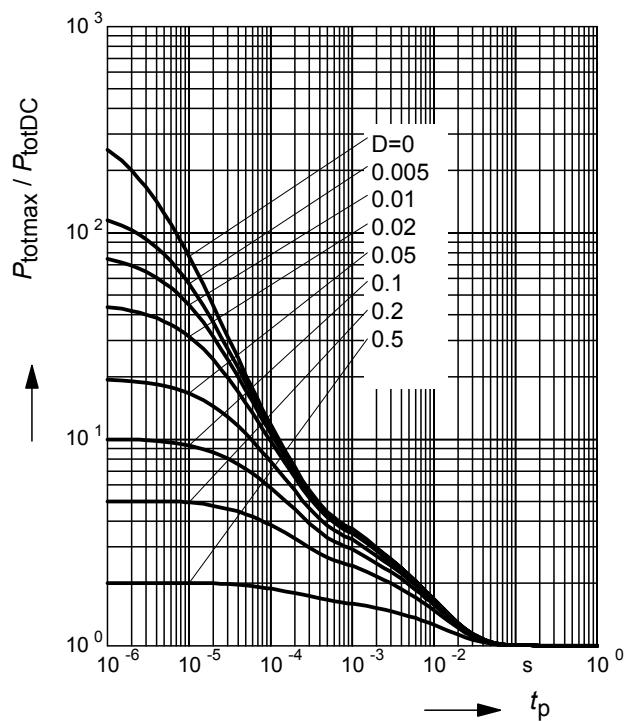
**Permissible Puls Load**  $R_{\text{thJS}} = f(t_p)$   
BC856U



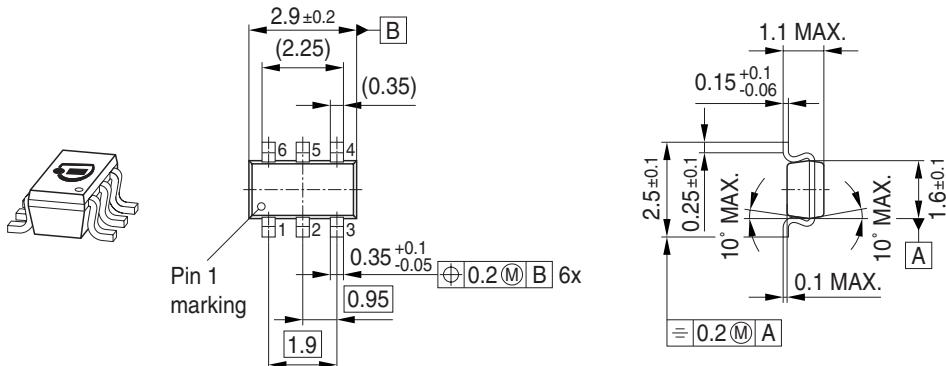
**Permissible Pulse Load**  
 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$   
BC856S, BC857S



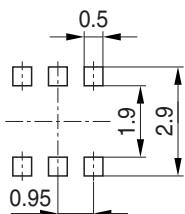
**Permissible Pulse Load**  
 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$   
BC856U



### Package Outline

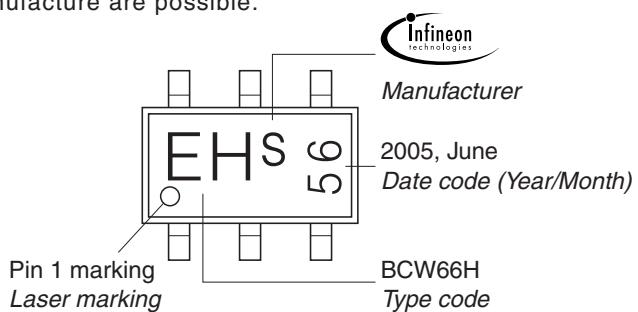


### Foot Print



### Marking Layout (Example)

Small variations in positioning of Date code, Type code and Manufacture are possible.

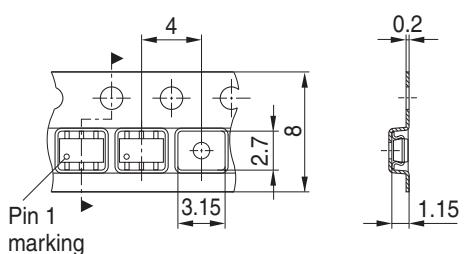


### Standard Packing

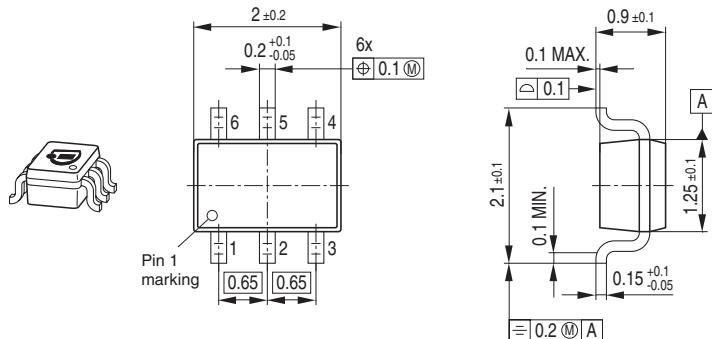
Reel ø180 mm = 3.000 Pieces/Reel

Reel ø330 mm = 10.000 Pieces/Reel

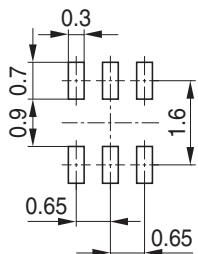
For symmetric types no defined Pin 1 orientation in reel.



### Package Outline

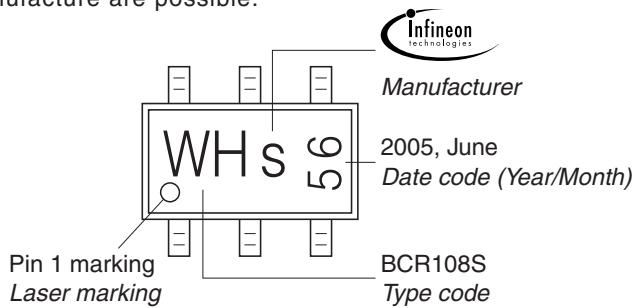


### Foot Print



### Marking Layout (Example)

Small variations in positioning of Date code, Type code and Manufacture are possible.

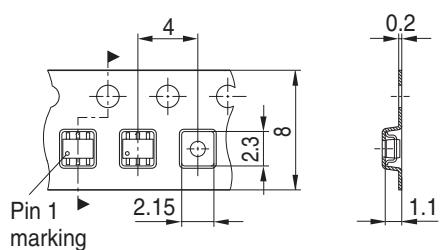


### Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel

Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.



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